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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	25MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	22
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-VQFN Exposed Pad
Supplier Device Package	32-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32hg310f32g-b-qfn32r

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1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32HG310 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (°C)	Package
EFM32HG310F32G-B-QFN32	32	8	25	1.98 - 3.8	-40 - 85	QFN32
EFM32HG310F64G-B-QFN32	64	8	25	1.98 - 3.8	-40 - 85	QFN32

Adding the suffix 'R' to the part number (e.g. EFM32HG310F32G-B-QFN32R) denotes tape and reel.

Visit www.silabs.com for information on global distributors and representatives.

There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 μ DMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32HG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32HG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32HG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 Low Energy USB

The unique Low Energy USB peripheral provides a full-speed USB 2.0 compliant device controller and PHY with ultra-low current consumption. The device supports both full-speed (12MBit/s) and low speed (1.5MBit/s) operation, and includes a dedicated USB oscillator with clock recovery mechanism for crystal-free operation. No external components are required. The Low Energy Mode ensures the current consumption is optimized and enables USB communication on a strict power budget. The USB device includes an internal dedicated descriptor-based Scatter/Gather DMA and supports up to 3 OUT endpoints and 3 IN endpoints, in addition to endpoint 0. The on-chip PHY includes software controllable pull-up and pull-down resistors.

2.1.11 Inter-Integrated Circuit Interface (I2C)

The I²C module provides an interface between the MCU and a serial I²C-bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s.



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD} = 3.0 V, T_{AMB} =85°C		1.6	3.50	μΑ
	EM3 current EM3 current EM abl V _D	EM3 current (ULFRCO en- abled, LFRCO/LFXO disabled), V_{DD} = 3.0 V, T _{AMB} =25°C		0.6	0.90	μA
'EM3		EM3 current (ULFRCO en- abled, LFRCO/LFXO disabled), V_{DD} = 3.0 V, T _{AMB} =85°C		1.2	2.65	μA
I _{EM4}	EM4 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.02	0.035	μA
	EM4 current	V _{DD} = 3.0 V, T _{AMB} =85°C		0.18	0.480	μA

3.4.1 EM0 Current Consumption

Figure 3.1. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 24 MHz



Figure 3.2. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 21 MHz



Figure 3.5. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 6.6 MHz



3.4.2 EM1 Current Consumption

Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 24 MHz



Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz



Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz





Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
Vices	Output high volt- age (Production test	Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
VIOOH	DRIVEMODE = STANDARD)	Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
		Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
Vicei	Output low voltage (Production test	Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
VIOOL	DRIVEMODE = STANDARD)	Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V
		Sinking 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.25V _{DD}	V
I _{IOLEAK}	Input leakage cur- rent	High Impedance IO connected to GROUND or Vdd		±0.1	±40	nA
R _{PU}	I/O pin pull-up resis- tor			40		kOhm



Figure 3.16. Typical Low-Level Output Current, 3V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD





GPIO_Px_CTRL DRIVEMODE = HIGH



Figure 3.19. Typical High-Level Output Current, 3.8V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR _{LFXO}	Supported crystal equivalent series re- sistance (ESR)			30	120	kOhm
C _{LFXOL}	Supported crystal external load range		5		25	pF
I _{LFXO}	Current consump- tion for core and buffer after startup.	ESR=30 kOhm, C _L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t _{LFXO}	Start- up time.	ESR=30 kOhm, C _L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		1100		ms

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
f _{HFXO}	Supported frequen- cy, any mode		4		25	MHz
	Supported crystal	Crystal frequency 25 MHz		30	100	Ohm
ESR _{HFXO}	sistance (ESR)	Crystal frequency 4 MHz		400	1500	Ohm
9 _{mHFXO}	The transconduc- tance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C _{HFXOL}	Supported crystal external load range		5		25	pF
	Current consump-	4 MHz: ESR=400 Ohm, C _L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μA
I _{HFXO}	startup	25 MHz: ESR=30 Ohm, C _L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μA
t _{HFXO}	Startup time	25 MHz: ESR=30 Ohm, C _L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		785		μs

3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
f _{LFRCO}	Oscillation frequen- cy , V_{DD} = 3.0 V, T_{AMB} =25°C		31.3	32.768	34.3	kHz
t _{LFRCO}	Startup time not in- cluding software calibration			150		μs
I _{LFRCO}	Current consump- tion			361	492	nA
TUNESTEP _{L-} FRCO	Frequency step for LSB change in TUNING value			202		Hz

Figure 3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage







Figure 3.25. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature



3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		21 MHz frequency band	20.37	21.0	21.63	MHz
	Oscillation frequen-	14 MHz frequency band	13.58	14.0	14.42	MHz
f _{AUXHFRCO}	cy, V_{DD} = 3.0 V,	11 MHz frequency band	10.67	11.0	11.33	MHz
	T _{AMB} =25 C	7 MHz frequency band	6.40	6.60	6.80	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
t _{AUXHFRCO_settlir}	_g Settling time after start-up	f _{AUXHFRCO} = 14 MHz		0.6		Cycles
		21 MHz frequency band		52.8		kHz
	Frequency step	14 MHz frequency band		36.9		kHz
TUNESTEP _{AUX} HFRCO	for LSB change in	11 MHz frequency band		30.1		kHz
	I UNING value	7 MHz frequency band		18.0		kHz
		1 MHz frequency band		3.4		kHz



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
t _{ADCACQVDD3}	Required acquisi- tion time for VDD/3 reference		2			μs
	Startup time of ref- erence generator and ADC core in NORMAL mode			5		μs
tadcstart	Startup time of ref- erence generator and ADC core in KEEPADCWARM mode			1		μs
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
	Signal to Noise Ra- tio (SNR)	1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB
		1 MSamples/s, 12 bit, differen- tial, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		69		dB
SNRADC		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		67		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		70		dB
SINAD _{ADC}	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		58		dB

Figure 3.35. IDAC Sink Current as a function of voltage from IDAC_OUT



Figure 3.36. IDAC linearity





Figure 3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4



Response time , V_{cm} = 1.25V, CP+ to CP- = 100mV



Table 3.28. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Тур	Мах	Unit
f _{SCL}	SCL clock frequency	0		400 ¹	kHz
t _{LOW}	SCL clock low time	1.3			μs
t _{HIGH}	SCL clock high time	0.6			μs
t _{SU,DAT}	SDA set-up time	100			ns
t _{HD,DAT}	SDA hold time	8		900 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	0.6			μs
t _{HD,STA}	(Repeated) START condition hold time	0.6			μs
t _{SU,STO}	STOP condition set-up time	0.6			μs
t _{BUF}	Bus free time between a STOP and START condition	1.3			μs

¹For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32HG Reference Manual. ²The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}). ³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 5).

Table 3.29. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Тур	Max	Unit
f _{SCL}	SCL clock frequency	0		1000 ¹	kHz
t _{LOW}	SCL clock low time	0.5			μs
t _{HIGH}	SCL clock high time	0.26			μs
t _{SU,DAT}	SDA set-up time	50			ns
t _{HD,DAT}	SDA hold time	8			ns
t _{SU,STA}	Repeated START condition set-up time	0.26			μs
t _{HD,STA}	(Repeated) START condition hold time	0.26			μs
t _{SU,STO}	STOP condition set-up time	0.26			μs
t _{BUF}	Bus free time between a STOP and START condition	0.5			μs

¹For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32HG Reference Manual.

3.15 USB

The USB hardware in the EFM32HG310 passes all tests for USB 2.0 Full Speed certification. The test report will be distributed with application note "AN0046 - USB Hardware Design Guide" when ready.

Table 3.30. USB

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
V _{USBOUT}	USB regulator out- put voltage		3.1	3.4	3.7	V
	USB regulator out- put current	BIASPROG=0, T _{AMB} =25°C	55.7	79.4	104.1	mA
1		BIASPROG=1, T _{AMB} =25°C	66.0	95.9	126.4	mA
IUSBOUT		BIASPROG=2, T _{AMB} =25°C	94.6	146.5	188.1	mA
		BIASPROG=3, T _{AMB} =25°C	80.4	128.3	176.0	mA

3.16 Digital Peripherals

Table 3.31. Digital Peripherals

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
I _{USART}	USART current	USART idle current, clock en- abled		7.5		μΑ/ MHz
I _{LEUART}	LEUART current	LEUART idle current, clock en- abled		150		nA
I _{I2C}	I2C current	I2C idle current, clock enabled		6.25		µA/ MHz
I _{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		8.75		µA/ MHz
I _{PCNT}	PCNT current	PCNT idle current, clock en- abled		100		nA
I _{RTC}	RTC current	RTC idle current, clock enabled		100		nA
I _{AES}	AES current	AES idle current, clock enabled		2.5		μΑ/ MHz
I _{GPIO}	GPIO current	GPIO idle current, clock en- abled		5.31		μΑ/ MHz
I _{PRS}	PRS current	PRS idle current		2.81		µA/ MHz
I _{DMA}	DMA current	Clock enable		8.12		μΑ/ MHz

7 Revision History

7.1 Revision 1.00

December 4th, 2015

Updated all specs with results of full characterization.

Updated part number to revision B.

Added the USB electrical specifications table.

7.2 Revision 0.91

May 6th, 2015

Updated current consumption table for energy modes.

Updated GPIO max leakage current.

Updated startup time for HFXO and LFXO.

Updated current consumption for HFRCO and LFRCO.

Updated ADC current consumption.

Updated IDAC characteristics tables.

Updated ACMP internal resistance.

Updated VCMP current consumption.

7.3 Revision 0.90

March 16th, 2015

Note

This datasheet revision applies to a product under development. It's characteristics and specifications are subject to change without notice.

Corrected EM2 current consumption condition in Electrical Characteristics section.

Updated GPIO electrical characteristics.

Updated Max ESR_{HFXO} value for Crystal Frequency of 25 MHz.

Updated LFRCO plots.

Updated HFRCO table and plots.

Updated ADC table and temp sensor plot.

Added DMA current in Digital Peripherals section.

Updated block diagram.

Updated Package dimensions table.

Corrected leadframe type to matte-Sn.

7.4 Revision 0.20

December 11th, 2014

Preliminary Release.

B Contact Information

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